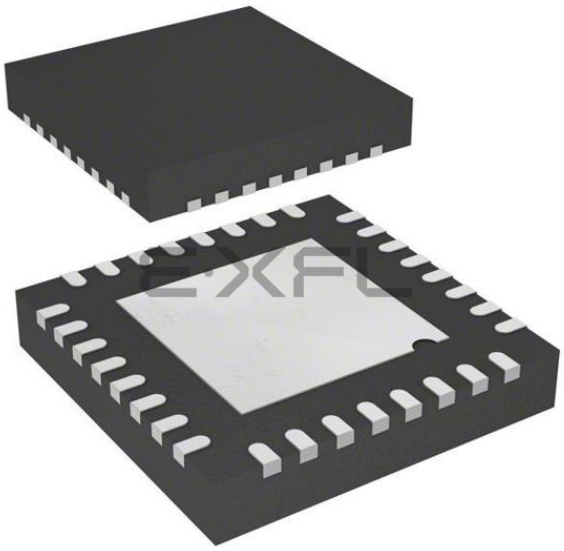

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	STM8A
Core Size	8-Bit
Speed	24MHz
Connectivity	I²C, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	25
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	6K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 7x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 150°C (TA)
Mounting Type	Surface Mount
Package / Case	32-VFQFN Exposed Pad
Supplier Device Package	32-VFQFPN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm8af62a6udy

List of tables

1 Introduction

This datasheet refers to the STM8AF526x/8x/Ax and STM8AF6269/8x/Ax products with 32 to 128 Kbyte of program memory.

In the order code, the letter ‘F’ refers to product versions with Flash and data EEPROM and ‘P’ to product versions with FASTROM. The identifiers ‘F’ and ‘P’ do not coexist in a given order code.

The datasheet contains the description of family features, pinout, electrical characteristics, mechanical data and ordering information.

- For complete information on the STM8A microcontroller memory, registers and peripherals, please refer to STM8S series and STM8AF series 8-bit microcontrollers reference manual (RM0016).
- For information on programming, erasing and protection of the internal Flash memory please refer to the STM8S and STM8A Flash programming manual (PM0051).
- For information on the debug and SWIM (single wire interface module) refer to the STM8 SWIM communication protocol and debug module user manual (UM0470).
- For information on the STM8 core, please refer to the STM8 CPU programming manual (PM0044).

5 Product overview

This section is intended to describe the family features that are actually implemented in the products covered by this datasheet.

For more detailed information on each feature please refer to STM8S series and STM8AF series 8-bit microcontrollers reference manual (RM0016).

5.1 STM8A central processing unit (CPU)

The 8-bit STM8A core is a modern CISC core and has been designed for code efficiency and performance. It contains 21 internal registers (six directly addressable in each execution context), 20 addressing modes including indexed indirect and relative addressing and 80 instructions.

5.1.1 Architecture and registers

- Harvard architecture
- 3-stage pipeline
- 32-bit wide program memory bus with single cycle fetching for most instructions
- X and Y 16-bit index registers, enabling indexed addressing modes with or without offset and read-modify-write type data manipulations
- 8-bit accumulator
- 24-bit program counter with 16-Mbyte linear memory space
- 16-bit stack pointer with access to a 64 Kbyte stack
- 8-bit condition code register with seven condition flags for the result of the last instruction.

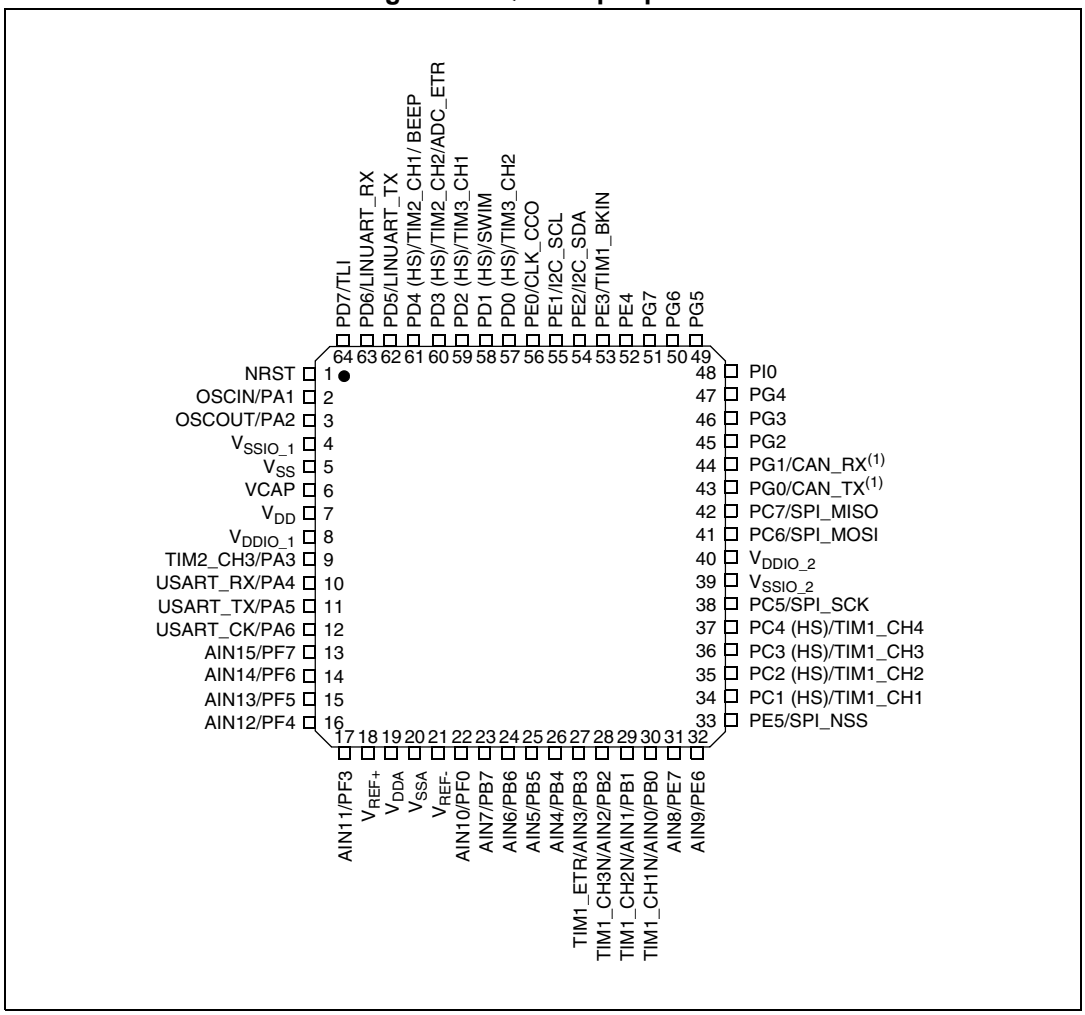
5.1.2 Addressing

- 20 addressing modes
- Indexed indirect addressing mode for look-up tables located anywhere in the address space
- Stack pointer relative addressing mode for efficient implementation of local variables and parameter passing

5.1.3 Instruction set

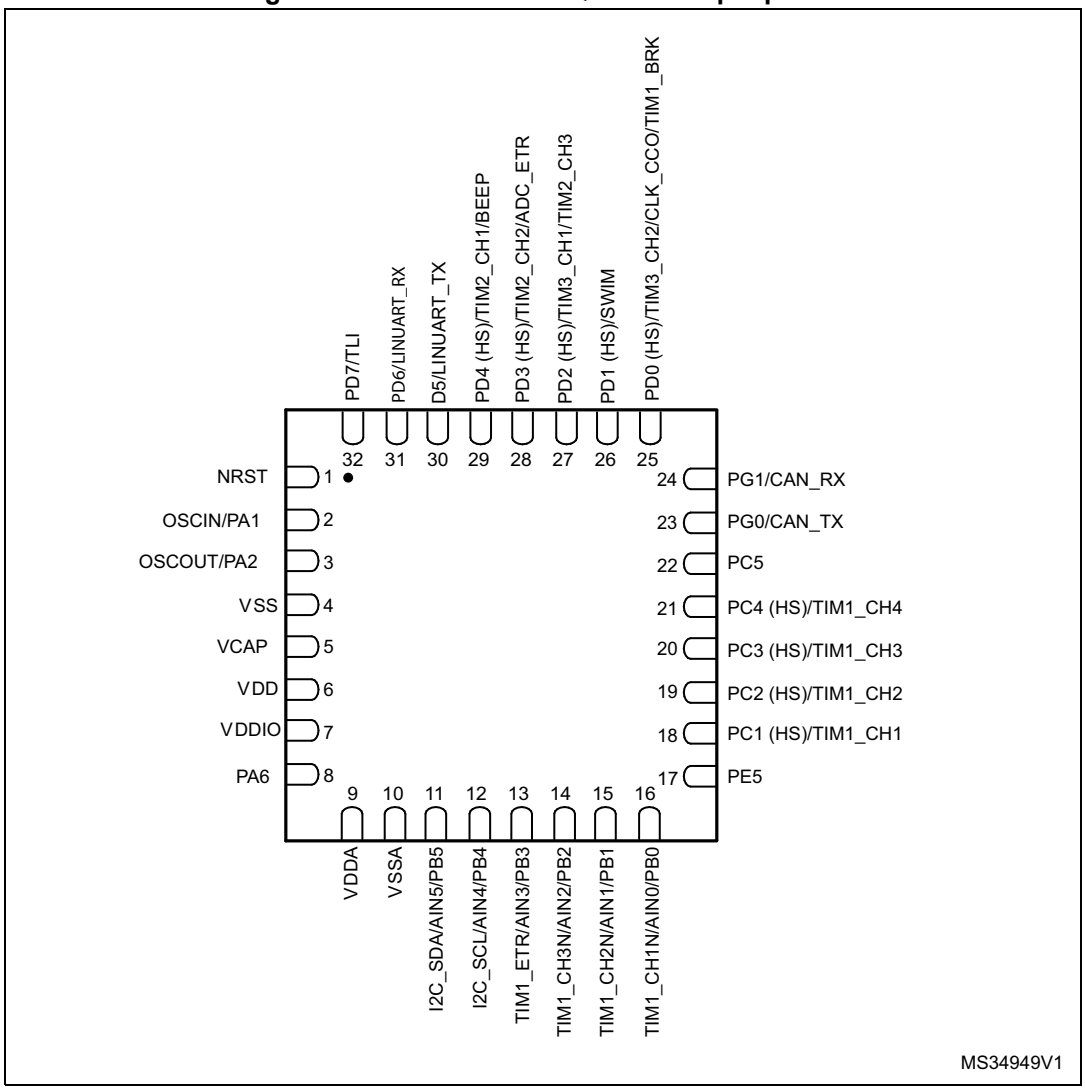
- 80 instructions with 2-byte average instruction size
- Standard data movement and logic/arithmetic functions
- 8-bit by 8-bit multiplication
- 16-bit by 8-bit and 16-bit by 16-bit division
- Bit manipulation
- Data transfer between stack and accumulator (push/pop) with direct stack access
- Data transfer using the X and Y registers or direct memory-to-memory transfers

Figure 4. LQFP 64-pin pinout



1. The CAN interface is only available on STM8AF52xx product lines.
2. HS stands for high sink capability.

Figure 7. STM8AF52x6 VFQFPN32 32-pin pinout



1. The following I/O ports are not automatically configured by hardware: PA3, PA4, PA5, PA6, PF4, PB6, PB7, PE0, PE1, PE2, PE3, PE6, PE7. As a consequence, they must be put into one of the following configurations by software:
   - configured as input with internal pull-up/down resistor,
   - configured as output push-pull low.
2. HS stands for high sink capability.

Table 11. STM8AF526x/8x/Ax and STM8AF6269/8x/Ax pin description

Pin number					Pin name	Type	Input			Output				Main function (after reset)	Default alternate function	Alternate function after remap [option bit]
LQFP80	LQFP64	LQFP48	STM8AF62xx LQFP32/VFQFPN32	STM8AF52x6 VFQFPN32			Floating	Wpu	Ext. interrupt	High sink	Speed	OD	PP			
1	1	1	1	1	NRST	I/O	-	**X**	-	-	-	-	-	Reset		-
2	2	2	2	2	PA1/OSCIN(1)	I/O	**X**	X	-	-	O1	X	X	**Port A1**	Resonator/ crystal in	-
3	3	3	3	3	PA2/OSCOUT	I/O	**X**	X	X	-	O1	X	X	**Port A2**	Resonator/ crystal out	-
4	4	4	-	-	V_{SSIO_1}	S	-	-	-	-	-	-	-	I/O ground		-
5	5	5	4	4	V_{SS}	S	-	-	-	-	-	-	-	Digital ground		-
6	6	6	5	5	VCAP	S	-	-	-	-	-	-	-	1.8 V regulator capacitor		-
7	7	7	6	6	V_{DD}	S	-	-	-	-	-	-	-	Digital power supply		-
8	8	8	7	7	V_{DDIO_1}	S	-	-	-	-	-	-	-	I/O power supply		-
9	9	9	-	-	PA3/TIM2_CH3	I/O	**X**	X	X	-	O1	X	X	**Port A3**	Timer 2 - channel 3	TIM3_CH1 [AFR1]
10	10	10	-	-	PA4/USART_RX	I/O	**X**	X	X	-	O3	X	X	**Port A4**	USART receive	-
11	11	11	-	-	PA5/USART_TX	I/O	**X**	X	X	-	O3	X	X	**Port A5**	USART transmit	-
12	12	12	-	8	PA6/USART_CK (2)	I/O	**X**	X	X	-	O3	X	X	**Port A6**	USART synchro nous clock	-
13	-	-	-	-	PH0	I/O	X	X	-	HS	O3	X	X	**Port H0**	-	-
14	-	-	-	-	PH1	I/O	**X**	X	-	HS	O3	X	X	**Port H1**	-	-
15	-	-	-	-	PH2	I/O	**X**	X	-	-	O1	X	X	**Port H2**	-	-
16	-	-	-	-	PH3	I/O	**X**	X	-	-	O1	X	X	**Port H3**	-	-
17	13	-	-	-	PF7/AIN15	I/O	**X**	X	-	-	O1	X	X	**Port F7**	Analog input 15	-
18	14	-	-	-	PF6/AIN14	I/O	**X**	X	-	-	O1	X	X	**Port F6**	Analog input 14	-
19	15	-	-	-	PF5/AIN13	I/O	**X**	X	-	-	O1	X	X	**Port F5**	Analog input 13	-
20	16	-	8	-	PF4/AIN12	I/O	**X**	X	-	-	O1	X	X	**Port F4**	Analog input 12	-
21	17	-	-	-	PF3/AIN11	I/O	**X**	X	-	-	O1	X	X	**Port F3**	Analog input 11	-

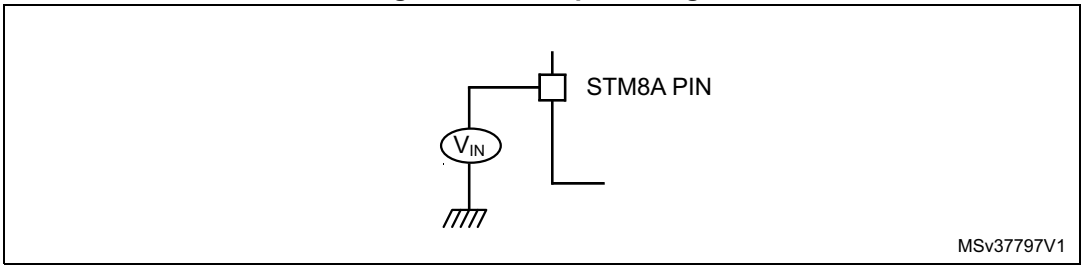
Table 14. General hardware register map (continued)

Address	Block	Register label	Register name	Reset status
0x00 5400	ADC	ADC _CSR	ADC control/status register	0x00
0x00 5401		ADC_CR1	ADC configuration register 1	0x00
0x00 5402		ADC_CR2	ADC configuration register 2	0x00
0x00 5403		ADC_CR3	ADC configuration register 3	0x00
0x00 5404		ADC_DRH	ADC data register high	0xXX
0x00 5405		ADC_DRL	ADC data register low	0xXX
0x00 5406		ADC_TDRH	ADC Schmitt trigger disable register high	0x00
0x00 5407		ADC_TDRL	ADC Schmitt trigger disable register low	0x00
0x00 5408 to 0x00 541F	Reserved area (24 bytes)			
0x00 5420	beCAN	CAN_MCR	CAN master control register	0x02
0x00 5421		CAN_MSR	CAN master status register	0x02
0x00 5422		CAN_TSR	CAN transmit status register	0x00
0x00 5423		CAN_TPR	CAN transmit priority register	0x0C
0x00 5424		CAN_RFR	CAN receive FIFO register	0x00
0x00 5425		CAN_IER	CAN interrupt enable register	0x00
0x00 5426		CAN_DGR	CAN diagnosis register	0x0C
0x00 5427		CAN_FPSR	CAN page selection register	0x00
0x00 5428		CAN_P0	CAN paged register 0	0xXX(3)
0x00 5429		CAN_P1	CAN paged register 1	0xXX(3)
0x00 542A		CAN_P2	CAN paged register 2	0xXX(3)
0x00 542B		CAN_P3	CAN paged register 3	0xXX(3)
0x00 542C		CAN_P4	CAN paged register 4	0xXX(3)
0x00 542D		CAN_P5	CAN paged register 5	0xXX(3)
0x00 542E		CAN_P6	CAN paged register 6	0xXX(3)
0x00 542F		CAN_P7	CAN paged register 7	0xXX(3)
0x00 5430		CAN_P8	CAN paged register 8	0xXX(3)
0x00 5431		CAN_P9	CAN paged register 9	0xXX(3)
0x00 5432		CAN_PA	CAN paged register A	0xXX(3)
0x00 5433		CAN_PB	CAN paged register B	0xXX(3)
0x00 5434		CAN_PC	CAN paged register C	0xXX(3)
0x00 5435		CAN_PD	CAN paged register D	0xXX(3)
0x00 5436		CAN_PE	CAN paged register E	0xXX(3)

10.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 10*.

Figure 10. Pin input voltage



10.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 20: Voltage characteristics*, *Table 21: Current characteristics* and *Table 22: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect the device's reliability. The device's mission profile (application conditions) is compliant with the JEDEC JESD47 qualification standard, extended mission profiles are available on demand.

Table 20. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
V_{DDx} - V_{SS}	Supply voltage (including V_{DDA} and V_{DDIO})(1)	-0.3	6.5	V
V_{IN}	Input voltage on true open drain pins (PE1, PE2)(2)	V_{SS} - 0.3	6.5	
	Input voltage on any other pin(2)	V_{SS} - 0.3	V_{DD} + 0.3	
$\lvert V_{DDx} - V_{DD} \rvert$	Variations between different power pins	-	50	mV
$\lvert V_{SSx} - V_{SS} \rvert$	Variations between all the different ground pins	-	50	
V_{ESD}	Electrostatic discharge voltage	see *Absolute maximum ratings (electrical sensitivity) on page 88*		

1. All power (V_{DD}, V_{DDIO}, V_{DDA}) and ground (V_{SS}, V_{SSIO}, V_{SSA}) pins must always be connected to the external power supply
2. $I_{INJ(PIN)}$ must never be exceeded. This is implicitly insured if V_{IN} maximum is respected. If V_{IN} maximum cannot be respected, the injection current must be limited externally to the $I_{INJ(PIN)}$ value. A positive injection is induced by $V_{IN} > V_{DD}$ while a negative injection is induced by $V_{IN} < V_{SS}$. For true open-drain pads, there is no positive injection current, and the corresponding V_{IN} maximum must always be respected

Table 27. Total current consumption in Halt and Active-halt modes. General conditions for V_{DD} applied. T_A = -40 °C to 55 °C unless otherwise stated

Symbol	Parameter	Conditions			Typ	Max	Unit
		Main voltage regulator (MVR)(1)	Flash mode(2)	Clock source and temperature condition			
$I_{DD(H)}$	Supply current in Halt mode	Off	Power-down	Clocks stopped	5	35(3)	µA
				Clocks stopped, T_A = 25 °C	5	25	
$I_{DD(AH)}$	Supply current in Active-halt mode with regulator on	On	Power-down	External clock 16 MHz f_{MASTER} = 125 kHz	770	900(3)	
				LSI clock 128 kHz	150	230(3)	
	Supply current in Active-halt mode with regulator off	Off	Power-down	LSI clock 128 kHz	25	42(3)	
				LSI clock 128 kHz, T_A = 25 °C	25	30	
$t_{WU(AH)}$	Wakeup time from Active-halt mode with regulator on	On	Operating mode	T_A = -40 to 150 °C	10	30(3)	µs
	Wakeup time from Active-halt mode with regulator off	Off			50	80(3)	

1. Configured by the REGAH bit in the CLK_ICKR register.
2. Configured by the AHALT bit in the FLASH_CR1 register.
3. Guaranteed by characterization results, not tested in production.

Current consumption for on-chip peripherals

Table 28. Oscillator current consumption

Symbol	Parameter	Conditions		Typ	Max(1)	Unit
$I_{DD(OSC)}$	HSE oscillator current consumption(2)	Quartz or ceramic resonator, CL = 33 pF V_{DD} = 5 V	f_{OSC} = 24 MHz	1	2.0(3)	mA
			f_{OSC} = 16 MHz	0.6	-	
			f_{OSC} = 8 MHz	0.57	-	
$I_{DD(OSC)}$	HSE oscillator current consumption(2)	Quartz or ceramic resonator, CL = 33 pF V_{DD} = 3.3 V	f_{OSC} = 24 MHz	0.5	1.0(3)	
			f_{OSC} = 16 MHz	0.25	-	
			f_{OSC} = 8 MHz	0.18	-	

1. During startup, the oscillator current consumption may reach 6 mA.
2. The supply current of the oscillator can be further optimized by selecting a high quality resonator with small R_m value. Refer to crystal manufacturer for more details
3. Informative data.

Table 29. Programming current consumption

Symbol	Parameter	Conditions	Typ	Max	Unit
$I_{DD(PROG)}$	Programming current	V_{DD} = 5 V, -40 °C to 150 °C, erasing and programming data or Flash program memory	1.0	1.7	mA

Table 30. Typical peripheral current consumption V_{DD} = 5.0 V(1)

Symbol	Parameter	Typ. f_{master} = 2 MHz	Typ. f_{master} = 16 MHz	Typ. f_{master} =24 MHz	Unit
$I_{DD(TIM1)}$	TIM1 supply current(2)	0.03	0.23	0.34	mA
$I_{DD(TIM2)}$	TIM2 supply current (2)	0.02	0.12	0.19	
$I_{DD(TIM3)}$	TIM3 supply current(2)	0.01	0.1	0.16	
$I_{DD(TIM4)}$	TIM4 supply current(2)	0.004	0.03	0.05	
$I_{DD(USART)}$	USART supply current(2)	0.03	0.09	0.15	
$I_{DD(LINUART)}$	LINUART supply current(2)	0.03	0.11	0.18	
$I_{DD(SPI)}$	SPI supply current(2)	0.01	0.04	0.07	
$I_{DD(I^2C)}$	I^2C supply current(2)	0.02	0.06	0.91	
$I_{DD(CAN)}$	CAN supply current(3)	0.06	0.30	0.40	
$I_{DD(AWU)}$	AWU supply current(2)	0.003	0.02	0.05	
$I_{DD(TOT\_DIG)}$	All digital peripherals on	0.22	1	2.4	
$I_{DD(ADC)}$	ADC supply current when converting(4)	0.93	0.95	0.96	

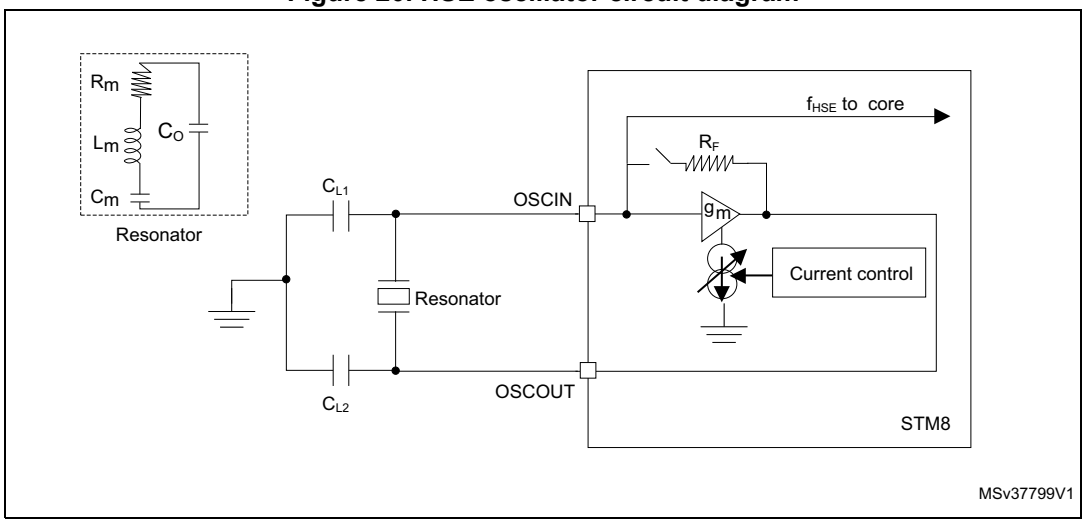
1. Typical values not tested in production. Since the peripherals are powered by an internally regulated, constant digital supply voltage, the values are similar in the full supply voltage range.
2. Data based on a differential I_{DD} measurement between no peripheral clocked and a single active peripheral. This measurement does not include the pad toggling consumption.
3. Data based on a differential IDD measurement between reset configuration (CAN disabled) and a permanent CAN data transmit sequence in loopback mode at 1 MHz. This measurement does not include the pad toggling consumption.
4. Data based on a differential I_{DD} measurement between reset configuration and continuous A/D conversions.

Table 32. HSE oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R_F	Feedback resistor	-	-	220	-	kΩ
C_{L1}/C_{L2} (1)	Recommended load capacitance	-	-	-	20	pF
g_m	Oscillator trans conductance	-	5	-	-	mA/V
$t_{SU(HSE)}$ (2)	Startup time	V_{DD} is stabilized	-	2.8	-	ms

1. The oscillator needs two load capacitors, C_{L1} and C_{L2}, to act as load for the crystal. The total load capacitance (C_{Load}) is $(C_{L1} * C_{L2})/(C_{L1} + C_{L2})$. If $C_{L1} = C_{L2}$, $C_{load} = C_{L1/2}$. Some oscillators have built-in load capacitors, C_{L1} and C_{L2}.
2. This value is the startup time, measured from the moment it is enabled (by software) until a stabilized 24 MHz oscillation is reached. It can vary with the crystal type that is used.

Figure 20. HSE oscillator circuit diagram



HSE oscillator critical g_m formula

The crystal characteristics have to be checked with the following formula:

Equation 1

$$g_m \gg g_{mcrit}$$

where g_{mcrit} can be calculated with the crystal parameters as follows:

Equation 2

$$g_{mcrit} = (2 \times \Pi \times {}^{f}HSE)^2 \times R_m(2Co + C)^2$$

R_m: Notional resistance (see crystal specification)
L_m: Notional inductance (see crystal specification)
C_m: Notional capacitance (see crystal specification)
Co: Shunt capacitance (see crystal specification)
$C_{L1} = C_{L2} = C$: Grounded external capacitance

Low-speed internal RC oscillator (LSI)

Subject to general operating conditions for V_{DD} and T_A.

Table 34. LSI oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSI}	Frequency	-	112	128	144	kHz
$t_{su(LSI)}$	LSI oscillator wakeup time	-	-	-	7(1)	µs

1. Guaranteed by characterization results, not tested in production.

Figure 22. Typical LSI frequency vs V_{DD}

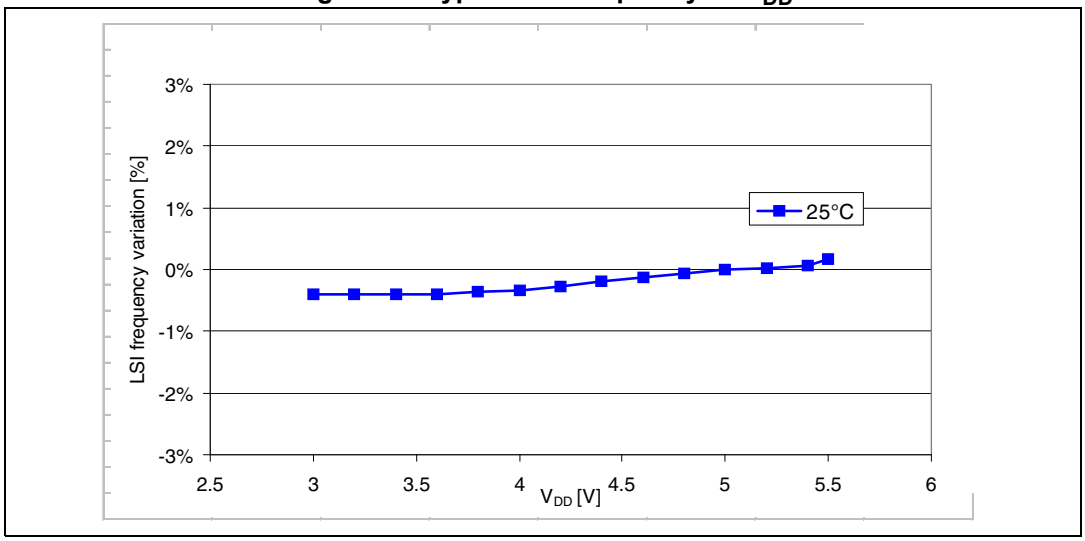


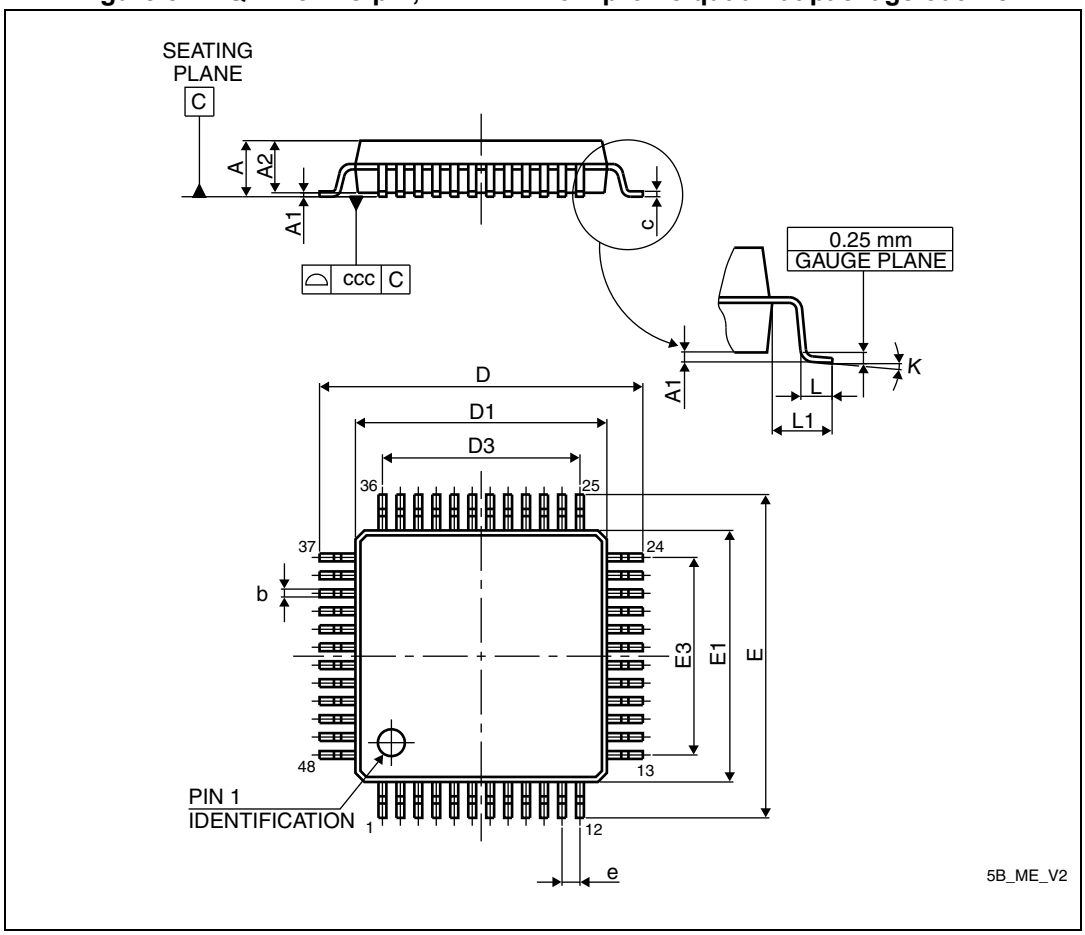
Table 37. Data memory

Symbol	Parameter	Condition	Min	Max	Unit
T_{WE}	Temperature for writing and erasing	-	-40	150	°C
N_{WE}	Data memory endurance(1) (erase/write cycles)	T_A = 25 °C	300 k	-	cycles
		T_A = -40°C to 125 °C	100 k(2)	-	
t_{RET}	Data retention time	T_A = 25 °C	40(2)(3)	-	years
		T_A = 55 °C	20(2)(3)	-	

1. The physical granularity of the memory is four bytes, so cycling is performed on four bytes even when a write/erase operation addresses a single byte.
2. More information on the relationship between data retention time and number of write/erase cycles is available in a separate technical document.
3. Retention time for 256B of data memory after up to 1000 cycles at 125 °C.

11.3 LQFP48 package information

Figure 51. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline



1. Drawing is not to scale.

Table 53. VFQFPN32 - 32-pin, 5 x 5 mm, 0.5 mm pitch very thin profile fine pitch quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	0.800	0.900	1.000	0.0315	0.0354	0.0394
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
A3	-	0.200	-	-	0.0079	-
b	0.180	0.250	0.300	0.0071	0.0098	0.0118
D	4.850	5.000	5.150	0.1909	0.1969	0.2028
D2	3.500	3.600	3.700	0.1378	0.1417	0.1457
E	4.850	5.000	5.150	0.1909	0.1969	0.2028
E2	3.500	3.600	3.700	0.1378	0.1417	0.1457
e	-	0.500	-	-	0.0197	-
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
ddd	-	-	0.050	-	-	0.0020

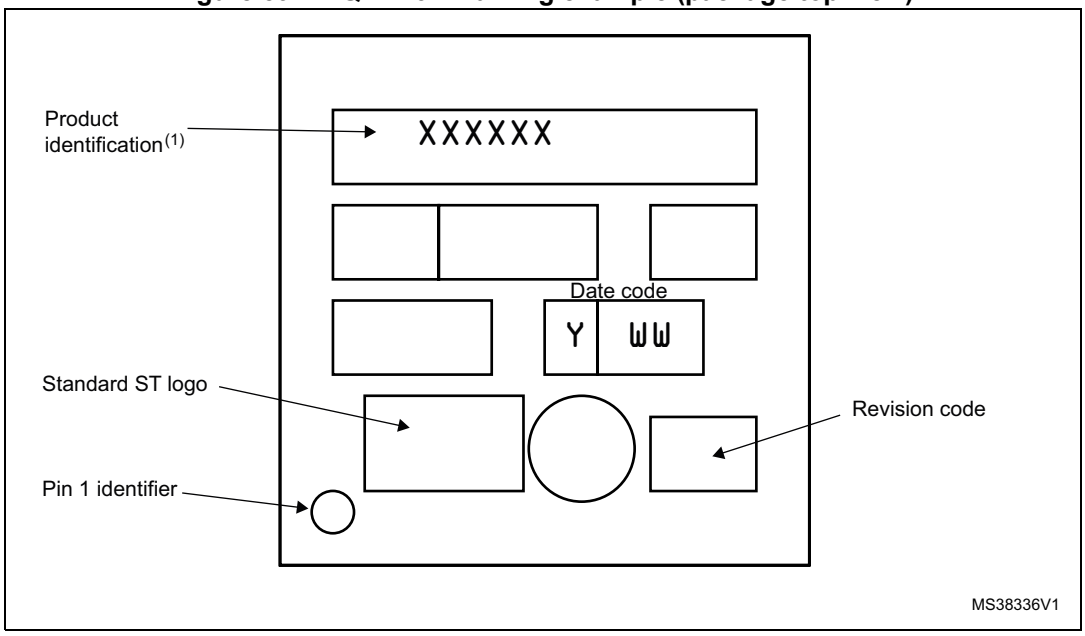
1. Values in inches are converted from mm and rounded to 4 decimal digits.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

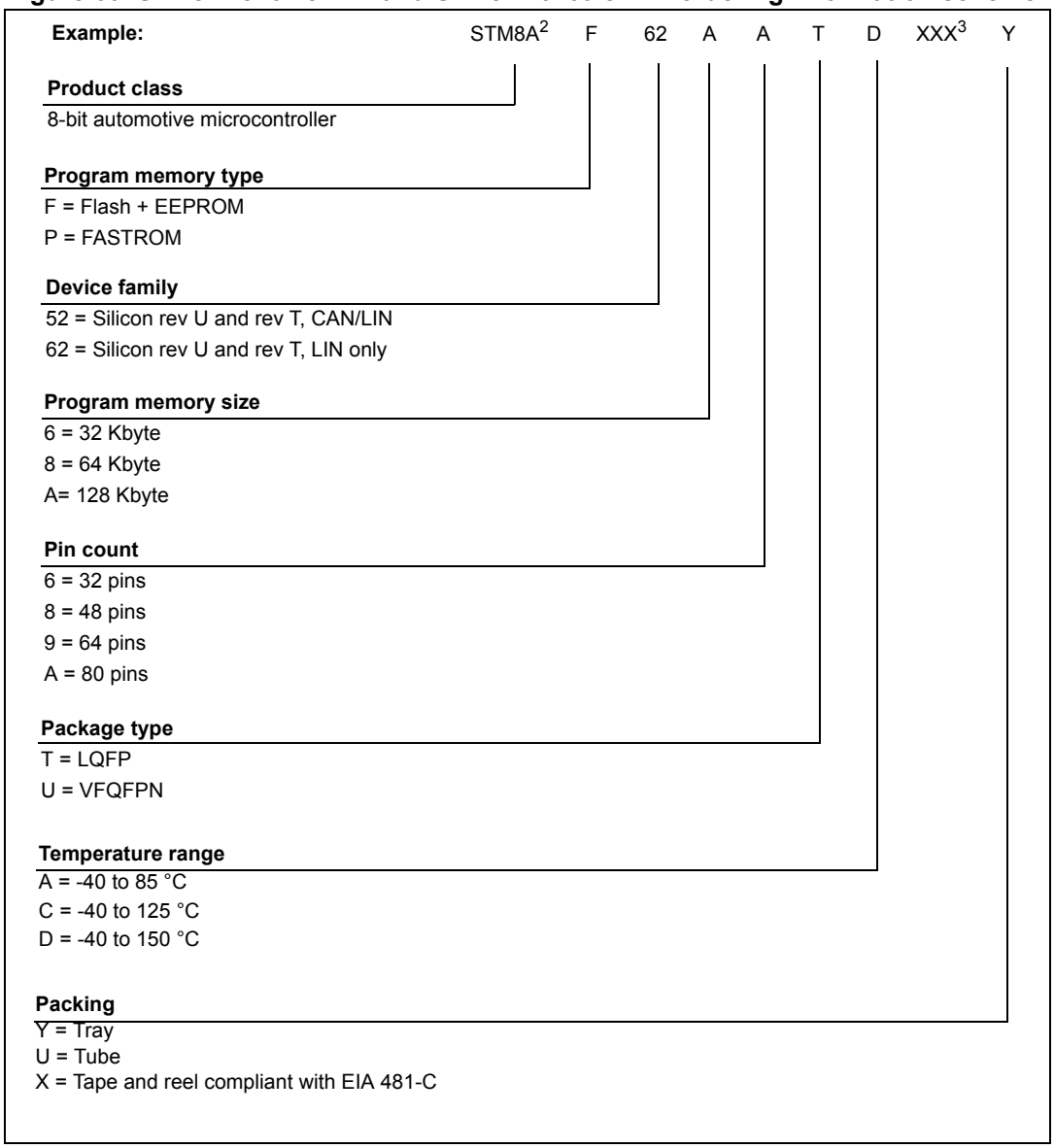
Figure 59. VFQFPN32 marking example (package top view)



1. Parts marked as "ES","E" or accompanied by an Engineering Sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's quality department must be contacted to run a qualification activity prior to any decision to use these engineering samples.

12 Ordering information

Figure 60. STM8AF526x/8x/Ax and STM8AF6269/8x/Ax ordering information scheme[1]



1. For a list of available options (e.g. memory size, package) and orderable part numbers or for further information on any aspect of this device, please go to *www.st.com* or contact the nearest ST Sales Office.
2. Qualified and characterized according to AEC Q100 and Q003 or equivalent, advanced screening according to AEC Q001 and Q002 or equivalent.
3. Customer specific FASTROM code or custom device configuration. This field shows 'SSS' if the device contains a super set silicon, usually equipped with bigger memory and more I/Os. This silicon is supposed to be replaced later by the target silicon.

Table 55. Document revision history (continued)

Date	Revision	Changes
22-Aug-2008	2 (continued)	*Table 18: Typ. IDD(WFI)HSI vs. VDD @ fCPU = 16 MHz, peripherals = off*: Replaced the source blocks 'simple USART', 'very low-end timer (timer 4)', and 'EEPROM' with 'LINUART', 'timer4' and 'reserved' respectively, added TMU registers. *Table 20: HSE oscillator circuit diagram*: Updated OPT6 and NOPT6, added OPT7 to 17 (TMU, BL) *Table 21: Typical HSI frequency vs VDD*: Updated OPT1 UBC[7:0], OPT4 CKAWUSEL, OPT4 PRSC [1:0], and OPT6, added OPT7 to 16 (TMU). *Table 23: Operating lifetime:* Amended footnotes. *Table 26: Total current consumption in Run, Wait and Slow mode. General conditions for VDD apply, TA = -40 °C to 150 °C:* Added parameter 'voltage and current operating conditions'. *Table 27: Total current consumption in Halt and Active-halt modes. General conditions for VDD applied. TA = -40 °C to 55 °C unless otherwise stated*: Amended footnotes. *Table 28: Oscillator current consumption*: Replaced. *Table 29: Programming current consumption*: Amended maximum data and footnotes. *Table 21: Current characteristics*: Replaced. *Table 22: Thermal characteristics:* Added and amended $I_{DD(RUN)}$ data; amended $I_{DD(WFI)}$ data; amended footnotes. *Table 32: HSE oscillator characteristics*: Filled in, amended maximum data and footnotes. *Figure 13* to *Figure 18*: info on peripheral activity added. *Table 33: HSI oscillator characteristics*: Modified f_{HSE_ext} data and added V_{HSEdhl} data. *Table 35: Flash program memory/data EEPROM memory*: Removed ACC_{HSI} parameters and replaced with ACC_{HS} parameters; amended data and footnotes. Amended data of '*RAM and hardware registers*' table. *Table 37: Data memory*: Updated names and data of N_{RW} and t_{RET} parameters. *Table 40: TIM 1, 2, 3, and 4 electrical specifications*: Added V_{OH} and V_{OL} parameters; Updated $I_{lkg\ ana}$ parameter. Removed: *Output driving current (standard ports), Output driving current (true open drain ports)*, and *Output driving current (high sink ports)*. *Table 46: EMI data*: Updated f_{ADC}, t_S, and t_{CONV} data. *Table: ADC accuracy for VDDA = 3.3 V*: removed the 4-MHz condition from all parameters. *Table 47: ESD absolute maximum ratings*: Removed the 4-MHz condition from all parameters; updated footnote 1 and removed footnote 2. *Table 51: LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package mechanical data*: Added data for T_A = 145 °C. *Figure 53*: Updated memory size, pin count and package type information.

Table 55. Document revision history (continued)

Date	Revision	Changes
16-Sep-2008	3	Replaced the salestype 'STM8H61xx' with 'STM8AH61xx on the first page. Added 'part numbers' to heading rows of *Table 1: Device summary*. Updated the 80-pin package silhouette on cover page in line with POA 0062342-revD. *Table 18*: Renamed 'TMU key registers 0-7 [7:0]' as 'TMU key registers 1-8 [7:0]' *Section 9*: Updated introductory text concerning option bytes which do not need to be saved in a complementary form. *Table 18*: Renamed the option bits 'TMU[0:3]', 'NTMU[0:3]', and 'TMU_KEY 0-7 [7:0]' as 'TMU[3:0]', 'NTMU[3:0]', and 'TMU_KEY 1-8 [7:0]' respectively. *Table 21*: Updated values of option byte 5 (HSECNT[7:0]); inverted the description of option byte 6 (TMU[3:0]); renamed option bytes 8 to 15 'TMU_KEY 0-7 [7:0]', as 'TMU_KEY 1-8 [7:0]'. Updated 80-pin package information in line with POA 0062342-revD in *Figure 45* and *Table 53*.
01-Jul-2009	4	Added 'STM8AH61xx' and 'STM8AH51xx to document header. Updated *: Features on page 1* (memories, timers, operating temperature, ADC and I/Os). Updated *Table 1: Device summary* Updated Kbyte value of program memory in *Section: Introduction* Changed the first two lines from the top in *Section: Description*. Updated *Figure 1: STM8AF526x/8x/Ax and STM8AF6269/8x/Ax block diagram* Updated *Section 5: Product overview* In *Figure 5: LQFP 48-pin pinout*, added USART function to pins 10, 11, and 12; added CAN Tx and CAN Rx functions to pins 35 and 36 respectively. *Section 6: Pinouts and pin description:* deleted the text below the *Table 10: Legend/abbreviation for the pin description table* *Table 11: STM8AF526x/8x/Ax and STM8AF6269/8x/Ax pin description:* 68th, 69th pin (LQFP80): replaced X with a dash for PP output and Added a table footnote. Updated *Figure 8: Register and memory map*. *Table 12: Memory model 128K:* updated footnote Deleted the *Table: Stack and RAM partitioning* *Table 17: STM8A interrupt table*: Updated priorities 13, 15, 17, 20 and 24 and changed table footnote Updated *Section 7: Memory and register map* Updated *Table: Data memory, Table: I/O static characteristics,* and *Table 39: NRST pin characteristics*. *Section 10.1.1: Minimum and maximum values:* added ambient temperature T_A = -40 °C Updated *Table 20: Voltage characteristics*. Updated *Table 21: Current characteristics*. Updated *Table 22: Thermal characteristics*. Updated *Table 24: General operating conditions*.

Table 55. Document revision history (continued)

Date	Revision	Changes
31-Mar-2014	10 (continued)	Added: – *Figure 7: STM8AF52x6 VFQFPN32 32-pin pinout;* – the caution in *Section 5.10: Input/output specifications,* – The table footnote “Not recommended for new designs” to *Table: STM8AF/H/P51xx product line-up with CAN* and *Table: STM8AF/H/P61xx product line-up without CAN.* – The figure footnotes to *Figure 7: STM8AF52x6 VFQFPN32 32-pin pinout* and *Figure: VFQFPN 32-lead very thin fine pitch quad flat no-lead package (5 x 5)*
13-Jun-2014	11	Added STM8AF52A6 part number.
09-Jun-2015	12	Added: – the third table footnote to *Table 25: Operating conditions at power-up/power-down*, – *Figure 47: LQFP80 marking example (package top view)*, – *Figure 50: LQFP64 marking example (package top view)*, – *Figure 53: LQFP48 marking example (package top view)*, – *Figure 56: LQFP32 marking example (package top view)*, – *Figure 59: VFQFPN32 marking example (package top view)*, – the footnote about the device marking to *Figure 60: STM8AF526x/8x/Ax and STM8AF6269/8x/Ax ordering information scheme1*. Removed STM8AF51xx and STM8AF61xx obsolete root part numbers, and consequently “H” products: – *Table 1: Device summary*, – *Section 1: Introduction*, – *Section 2: Description*, – *Section 3: Product line-up*, – *Table 12: Memory model 128K*, – *Section 10.3: Operating conditions*, – *Figure 60: STM8AF526x/8x/Ax and STM8AF6269/8x/Ax ordering information scheme1*. Moved *Section 11.6: Thermal characteristics* to *Section 11: Package information*. Updated: – the product naming in the document headers and captions, – the standard reference for EMI characteristics in *Table 46: EMI data*.
13-Jun-2016	13	Updated *Table 53: VFQFPN32 - 32-pin, 5 x 5 mm, 0.5 mm pitch very thin profile fine pitch quad flat package mechanical data*